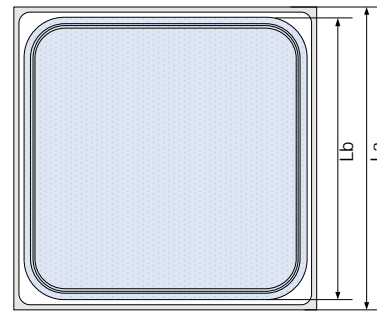


2SB183060MA LOW IR SCHOTTKY BARRIER DIODE CHIPS
DESCRIPTION

- ∅ 2SB183060MA is a schottky barrier diode chips fabricated in silicon epitaxial planar technology;
- ∅ Due to special schottky barrier structure, the chips have very low reverse leakage current (typical $I_R=0.002\text{mA}@ V_r=100\text{V}$) and maximum 150°C operation junction temperature;
- ∅ Low power losses, high efficiency;
- ∅ Guard ring construction for transient protection;
- ∅ High ESD capability;
- ∅ High surge capability;
- ∅ Packaged products are widely used in switching power suppliers, polarity protection circuits and other electronic circuits;
- ∅ Chip Size: 1830 μm X 1830 μm ;
- ∅ Chip Thickness: 280 \pm 20 μm ;


Chip Topography and Dimensions

 La: Chip Size: 1830 μm ;

 Lb: Pad Size: 1730 μm ;

ORDERING SPECIFICATIONS

Product Name	Specification
2SB183060MAYY	For Axial leads package

ABSOLUTE MAXIMUM RATINGS

Parameters	Symbol	Ratings	Unit
Maximum Repetitive Peak Reverse Voltage	VRRM	60	V
Average Forward Rectified Current	IFAV	5	A
Peak Forward Surge Current@8.3ms	IFSM	150	A
Maximum Operation Junction Temperature	TJ	150	°C
Storage Temperature Range	TSTG	-40~150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Parameters	Symbol	Test Conditions	Min.	Max.	Unit
Reverse Voltage	VBR	IR=0.5mA	60	--	V
Forward Voltage	VF	IF=5A	--	0.70	V
Reverse Current	IR	VR=60V	--	0.5	mA